

FDS8813NZ N-Channel PowerTrench[®] MOSFET 30V, 18.5A, 4.5m Ω

Features

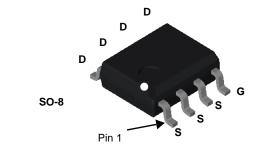
- Max $r_{DS(on)} = 4.5 m\Omega$ at $V_{GS} = 10V$, $I_D = 18.5A$
- Max $r_{DS(on)} = 6.0 m\Omega$ at $V_{GS} = 4.5 V$, $I_D = 16 A$
- HBM ESD protection level of 5.6KV typical (note 3)
- High performance trench technology for extremely low r_{DS(on)}
- High power and current handling capability
- RoHS compliant

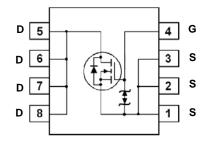


General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been especially tailored to minimize the on-state resistance.

This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.





MOSFET Maximum Ratings $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Ratings	Units	
V _{DS}	Drain to Source Voltage		30	V	
V _{GS}	Gate to Source Voltage		±20	V	
	Drain Current -Continuous	(Note 1a)	18.5	٨	
I _D	-Pulsed		74	— A	
E _{AS}	Single Pulse Avalanche Energy (N		337	mJ	
P _D	Power Dissipation	(Note 1a)	2.5	- w	
	Power Dissipation	(Note 1b)	1.0		
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C	

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	25	
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	(Note 1a)	50	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	(Note 1b)	125	

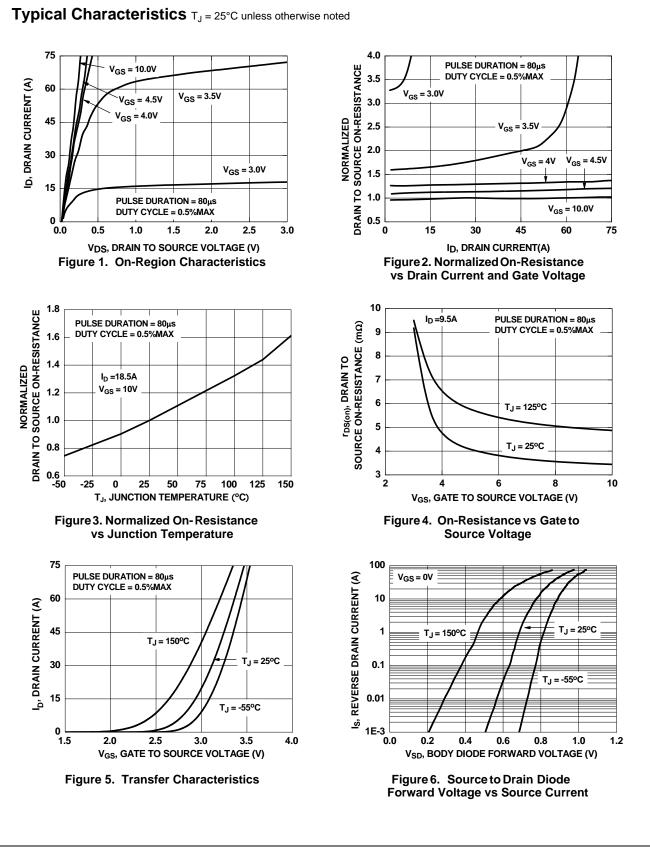
Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDS8813NZ	FDS8813NZ	13"	12mm	2500 units

May 2013

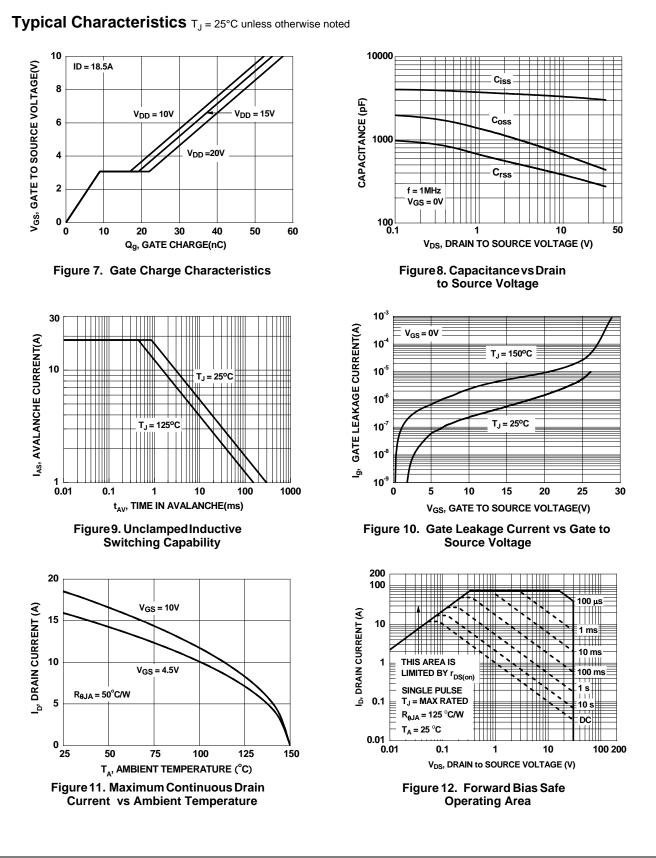
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in to Source Breakdown Voltage akdown Voltage Temperature efficient o Gate Voltage Drain Current te to Source Leakage Current	$I_D = 250\mu A$, referenced to 25°C $V_{DS} = 24V$, $V_{GS} = 0V$	30	20	1	mV/°C
akdown Voltage Temperature efficient o Gate Voltage Drain Current e to Source Leakage Current	$I_D = 250\mu A$, referenced to 25°C $V_{DS} = 24V$, $V_{GS} = 0V$		20	1	mV/°C
o Gate Voltage Drain Current e to Source Leakage Current				1	-
e to Source Leakage Current		-			μA
-	65 25			±10	μΑ
ISTICS (Note 2)		4	-	4	ļ .
			1		
te to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	1	1.8	3	V
e to Source Threshold Voltage	$I_D = 250 \mu A$, referenced to $25^{\circ}C$		-6		mV/°C
					-
tic Drain to Source On Resistance			4.7	6.0	mΩ
	$T_J = 125^{\circ}C$		5.1	6.6	
ward Transconductance	$V_{DS} = 5V, I_{D} = 18.5A$		74		S
racteristics					
			3115	4145	pF
	$V_{DS} = 15V, V_{GS} = 0V,$			-	pF
	-f = 1MHz				pF
	f = 1MHz	0.1			Ω
aracteristics					
n-On Delay Time			13	24	ns
e Time			8	16	ns
n-Off Delay Time	VGS = 100, TGEN = 032		39	63	ns
Time			7	14	ns
al Gate Charge	$V_{GS} = 0V$ to $10V$ $V_{DD} = 15V$		55	76	nC
al Gate Charge	$V_{GS} = 0V \text{ to } 5V$ $I_D = 18.5A$		28	40	nC
e to Source Gate Charge			9		nC
e to Drain "Miller" Charge			10		nC
Diode Characteristics					
	$V_{CS} = 0V$, $I_S = 2.1A$ (Note 2)		0.7	1.2	V
			-		ns
	— I _F = 18.5A, di/dt = 100A/μs				nC
	Itic Drain to Source On Resistance Itic Drain to Source On Resistance Itic Drain to Source On Resistance Itic Capacitance Itic Capacitance Itic Capacitance Itic Capacitance Itic Capacitance Itic Capacitance Itic Itic Itic Itic Itic Itic Itic Itic	Inperature CoefficientInperature CoefficientInperature CoefficientInperature CoefficientInperature CoefficientInperature CoefficientItic Drain to Source On Resistance $V_{GS} = 10V$, $I_D = 18.5A$ VGS = 10V, $I_D = 18.5A$, T_J = 125°C $V_{GS} = 10V$, $I_D = 18.5A$ ward Transconductance $V_{DS} = 5V$, $I_D = 18.5A$ racteristicsIti Capacitance rerese Transfer Capacitance $V_{DS} = 15V$, $V_{GS} = 0V$, f = 1MHzrecteristicsf = 1MHzaracteristicsInperature CapacitanceInperature CapacitanceIn-On Delay TimeInperature CapacitanceInperature CapacitanceIn-On Delay TimeV_DD = 15V, $I_D = 18.5A$ V_GS = 10V, $R_{GEN} = 6\Omega$ In-Onf Delay TimeInperature CapacitanceInperature CapacitanceIndicate ChargeV_GS = 0V to 10VV_DD = 15VIndicate ChargeV_GS = 0V to 5VInperature CapacitanceInterest CapacitanceInperature CapacitanceInperature CapacitanceInterest Capac	ID $I_D = 250 \mu A$, referenced to $25^{\circ} C$ tic Drain to Source On Resistance $V_{GS} = 10V, I_D = 18.5A$ $V_{GS} = 10V, I_D = 18.5A$ $V_{GS} = 10V, I_D = 18.5A$ ward Transconductance $V_{DS} = 5V, I_D = 18.5A$ racteristicsut Capacitance $V_{DS} = 5V, I_D = 18.5A$ ut Capacitance $V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$ rese Transfer Capacitance $f = 1MHz$ verse Transfer Capacitance $f = 1MHz$ e Resistance $f = 1MHz$ n-On Delay Time $V_{DD} = 15V, I_D = 18.5A$ n-Off Delay Time $V_{GS} = 0V \text{ to } 10V$ Time $V_{GS} = 0V \text{ to } 10V$ al Gate Charge $V_{GS} = 0V \text{ to } 5V$ at Gate Charge $V_{GS} = 0V \text{ to } 5V$ te to Source Gate Charge $V_{GS} = 0V \text{ to } 5V$ te to Drain "Miller" Charge $V_{GS} = 0V, I_S = 2.1A$ (Note 2)Verse Recovery Time V_{erse} Recovery Time $V_{erse} = 18.5A, di/dt = 100A/us$	Inperature CoefficientID 250μ A, referenced to 25° C-6ID $D = 250\mu$ A, referenced to 25° C-6ID $V_{GS} = 10V, I_D = 18.5A$ 3.8VGS = 10V, ID = 18.5A4.7VGS = 10V, ID = 18.5A, TJ = 125^{\circ}C5.1ward TransconductanceVDS = 5V, ID = 18.5A74racteristicsVDS = 5V, ID = 18.5A74racteristicsVDS = 15V, VGS = 0V, f = 1MHzaltic colspan="2">altic colspan="2"altic colspan="2"altic colspan="2"VDIC Colspan="2"altic colspan="2"	Inperature Coefficient Inperature Coefficient <thi< td=""></thi<>

3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied. 4. Starting $T_J = 25^{\circ}$ C, L = 3mH, $I_{AS} = 15A$, $V_{DD} = 30V$, $V_{GS} = 10V$.



FDS8813NZ Rev.C2

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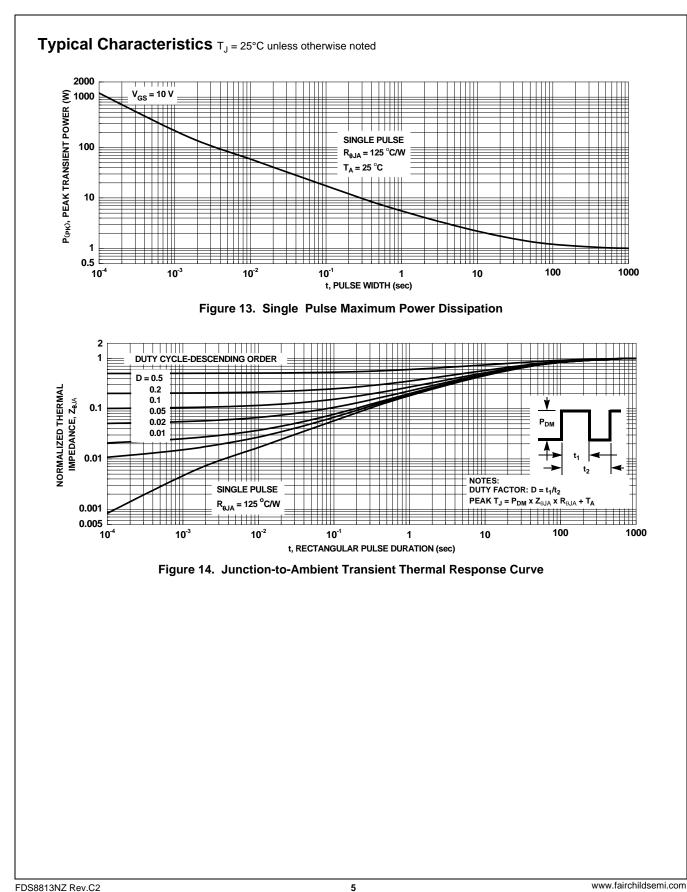


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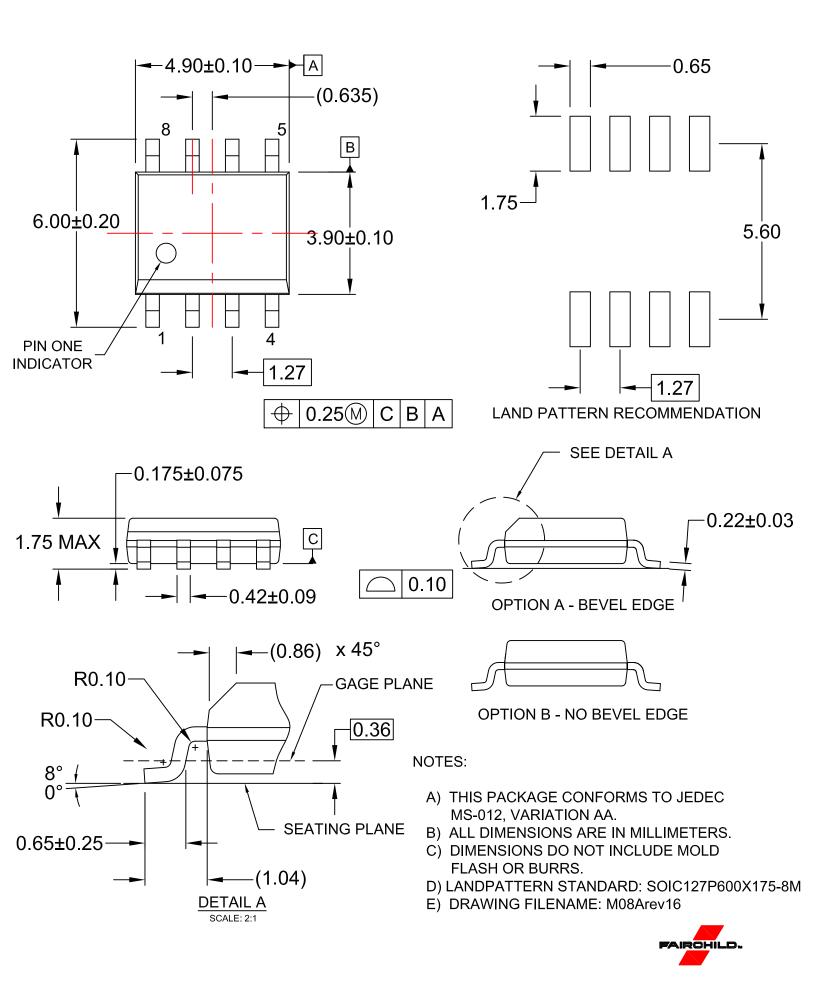
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